MBE growth and characterization of InGaN-based films and nanocolumns on Silicon substrates and GaN templates

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Outline

InN layers: MBE growth issues

Growth of InN-based thin films:

- InN/InGaN QWs on GaN

Growth of InN-based nanorods

- Self-assembled InN nanorods on different substrates
- Self-assembled InGaN nanorods
- Broad-emission nanostructures
- Self-assembled InGaN-based Qdisks
- Selective area growth (SAG) of InGaN Qdisks

Ordered NRs with a single InGaN/GaN QDisc